

Abstract of the Disclosure

FeRAM and a method for generating a reference voltage are disclosed. The ferroelectric memory device includes: a
5 memory cell unit having a plural memory cells equipping a ferroelectric capacitor and a first current gain transistor; a reference cell unit having a reference cell quipping a ferroelectric capacitor and a second current gain transistor; and a sense amp unit for comparing voltages, amplifying the
10 voltage difference and outputting data, wherein a size of the two ferroelectric capacitor in the memory cell and the reference cell is identical and a size of the first current gain transistor and the second current gain transistor is different. As mentioned above, the present invention can
15 generate a reference voltage by implementing different size of current gain transistors. Therefore, it can reduce time and cost to optimize a size of a ferroelectric capacitor for manufacturing high integrated 1T1C ReRAM.